

<b>Notice of References Cited</b>	Application/Control No. 10/713,489	Applicant(s)/Patent Under Reexamination MOY, ROBERT M.	
	Examiner Thanh-Truc Trinh	Art Unit 1753	Page 1 of 1

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*	B	US-5,944,913 A	08-1999	Hou et al.	136/255
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	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	Aiken, DJ; "InGaP/GaAs/Ge multi-junction solar cell efficiency improvements using epitaxial Germanium"; Photovoltaic Specialists Conference, 2000, Conference Record of the Twenty-Eight IEEE; 2000; pp. 994-997.
*	V	Nishioka et al.; "Temperature Characteristics of High Efficiency InGaP/InGa/Ge Triple-Junction Solar Cells Under Concentration; Photovoltaic Specialists Conference 2002, Conference Record of the Twenty-Ninth IEEE; May 19-24 2002, pp 955-958.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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